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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	Unassigned 10/540514
Confirmation Number	Unassigned
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First Named Inventor	Takenori OSADA
Art Unit	Unassigned
Examiner Name	Unassigned
Attorney Docket Number	Q88664

Sheet 1 of 1

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document
		Number	Kind Code ² (if known)		
		US			
		US			
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FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Foreign Patent Document			Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Translation ⁶
		Country Code ³	Number ⁴	Kind Code ⁵ (if known)			
		JP	06-163599	A	06-10-1994	NEC Corporation	
		JP	06-84959	A	03-25-1994	Fujitsu Ltd.	
		JP	2001-210819	A	08-03-2001	Hitachi Cable, Ltd.	

NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city, and/or country where published.	Translation ⁶
		Feng Zhao et al., "Hall and photoluminescence studies of effects of the thickness of an additional In _{0.3} Ga _{0.75} As layer in the center of In _{0.15} Ga _{0.85} As/Al _{0.25} Ga _{0.75} As/GaAs high electron mobility transistors", <i>Materials Science in Semiconductor Processing</i> , Vol. 5, February 2002, pp. 23-26.	
		U. Strauße et al., "Carrier mobilities in graded In _x Ga _{1-x} As/Al _{0.2} Ga _{0.8} As quantum wells for high electron mobility transistors", <i>Journal of Applied Physics</i> , Vol. 80, No. 1, July 1, 1996, pp. 322-325.	

Examiner Signature		Date Considered	
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹Applicant's unique citation designation number (optional). ²See Kind Codes of USPTO Patent Documents at www.uspto.gov, MPEP 901.04 or in the comment box of this document. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST. 3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to indicate here if English language Translation is attached.